TEXAS INSTRUMENTS Data sheet acquired from Harris Semiconductor

SCHS052A - Revised March 2002

## CMOS Analog Multiplexers/Demultiplexers

High-Voltage Types (20-Volt Rating)

CD4067B – Single 16-Channel Multiplexer/Demultiplexer

CD4097B — Differential 8-Channel Multiplexer/Demultiplexer

#### CD4067B and CD4097B CMOS

analog multiplexers/demultiplexers\* are digitally controlled analog switches having low ON impedance, low OFF leakage current, and internal address decoding. In addition, the ON resistance is relatively constant over the full input-signal range.

The CD4067B is a 16-channel multiplexer with four binary control inputs, A,B,C,D, and an inhibit input, arranged so that any combination of the inputs selects one switch.

The CD4097B is a differential 8-channel multiplexer having three binary control inputs A, B, C, and an inhibit input. The inputs permit selection of one of eight pairs of switches.

A logic "1" present at the inhibit input turns all channels off.

The CD4067 and CD4097 are supplied in 24-lead dual-in-line welded-seal ceramic packages (D suffix), 24-lead dual-in-line frit-seal ceramic packages (F suffix), 24-lead dual-in-line plastic packages (E suffix), 24-lead small-outline package (NSR suffix), and in chip form (H suffix).

When these devices are used as demultiplexers, the channel in/out terminals are the outputs and the common out/in terminals are the inputs.

Recommended Operating Conditions at  $T_A = 25^{\circ}C$  (Unless Otherwise Specified) For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges. Values shown apply to all types except as noted.

Characteristic	Min.	Max.	Units
Supply-Voltage Range (T <sub>A</sub> =Full Package- Temp. Range)	3	18	v
Multiplexer Switch Input Current Capability	-	25	mA
Output Load Resistance	100		·Ω

#### NOTE:

In certain applications, the external load-resistor current may include both V<sub>DD</sub> and signal-line components. To avoid drawing V<sub>DD</sub> current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from R<sub>ON</sub> values shown in ELECTRICAL CHARAC-TERISTICS CHART). No V<sub>DD</sub> current will flow through R<sub>L</sub> if the switch current flows into terminal 1 on the CD4067; terminals 1 and 17 on

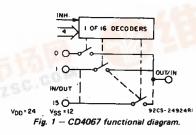
# the CD4097.

#### Features:

- Low ON resistance: 125 Ω (typ.) over 15 V<sub>p-p</sub> signal-input range for VDD-VSS=15 V
- High OFF resistance: channel leakage of ±10 pA (typ.) @ VDD-VSS=10 V
- Matched switch characteristics: RON=5 Ω (typ.) for VDD-VSS=15 V
- Very low quiescent power dissipation under all digital-control input and supply conditions: 0.2 µW (typ.) @ VDD-VSS=10 V
- Binary address decoding on chip
- 5-V, 10-V, and 15-V parametric ratings
- 100% tested for quiescent current at 20 V
- Standardized symmetrical output characteristics
- Maximum input current of 1 µA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

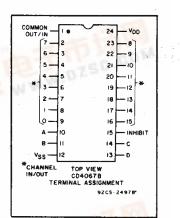
#### Applications:

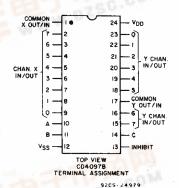
- Analog and digital multiplexing and demultiplexing
- A/D and D/A conversion
- Signal gating



CD4067 TRUTH TABLE

	604	007	INU						
A	в	с	D	Inh	Selected Channel				
х	X	X	X	1	None				
0	0	0	0	0	0				
1	0	0	0	.0.	1				
0	1	0	0	0	2				
1	1	0	0	0	3				
0	0	1	0	0	4				
1	0	1	0	0	5				
0	1	1	0	0	6				
1	1	1	0	0	.7				
0	0	0	1	0	8				
1	0	0	1	0	9				
0	1	0	1	0	10				
1	1	0	1	0	11				
0	0	1	1	0	12				
1	0	1	1	0	13				
0	1	1	1	0	14				
1	1	1	1	0	15				







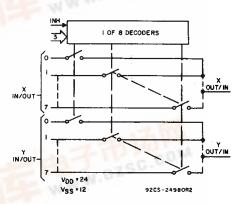
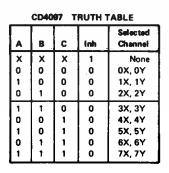


Fig. 2-CD4097 functional diagram.



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#### **ELECTRICAL CHARACTERISTICS**

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CHARAC TERISTIC			LIMITS AT INDICATED TEMPERATUR					ERATURES (ºĊ)				11	
	V <sub>is</sub>	V <sub>SS</sub>	V <sub>DD</sub>	-55	-40	+85	+125		+25		]·	I I I	∞ 
	(V)	(V)	(V)					Min.	Тур.	Max.		523	∞⊞
SIGNAL INF	PUTS (	Vis) AND OUT	PUTS (	v <sub>os</sub> )								8 21	∞⊞
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Max.			20	100	100	3000	3000	<b></b> :	0.08	100	1.		
ON-state Re		-			·						1		
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V <sub>SS</sub> ≪ V <sub>is</sub> ≪V <sub>DD</sub>		0	5	800	850	1200	1300	ļ —	470	1050			
ron Max.		0	10	310	330	520	550	<u>                                      </u>	180	400 ~	$\sim 0^{-1}$		
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Resistance						Í		]	1		·	(NO E) 25	sШ
(Between					ľ		1	1		1 .		8	1
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Channels)		0	10	_	_	-		,	10	-	$\Omega$	RESISTANCE	so
∆r <sub>on</sub>		0	15		_	-			5	· · · · · ·		e Z	
FF Chan-												CHANNEL ON	<b>•</b>
nel Leak- age Cur-												NY :	0
rent: Any									1	<b>.</b>		5	0
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OFF Max.		o	18		0.0*		<b></b>		±0.1	±100*		-	
or		U U	10	1 I I	00*	±100	0*	-	÷0.1	1100	nA	-	
All Chan- nels OFF								I				<i></i>	g. 4.
(Common						İ				ł			
OUT/IN)											Ì		
Max.						ļ							54
Capacitance:												a   30	04
Input, C <sub>is</sub>				-	~	-		-	5	- 1	:	1 m	
Output,													아
Cos												20	₀⊞
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CD4097		<b>J</b>	5		-	-	-		35		рг		°
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ropaga-		R <sub>L</sub> = 200 KΩ	5	_	_		_		30	60		L	-10
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to Output										20		i Fi	g. 5
	(ADDI	RESS or INHIB	T) Va	L		L	1. 1.2			L	L	ļ	
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nput Low	ļ	to Vee		<u> </u>	1.5					1.5		· · ·	AN
Voltage, V <sub>IL</sub> Max.	=VDD	ιο VSS Ι <sub>4S</sub> <2 μΑ	10	<b> </b>	3			:		3		e   60	1.1
	thru	on all OFF	15		4			-	<b>—</b> .	4			
nput High	1 ΚΩ	Channels	5		3.5	\$	· ·	3.5		-	1 <sup>×</sup>	8 50	•
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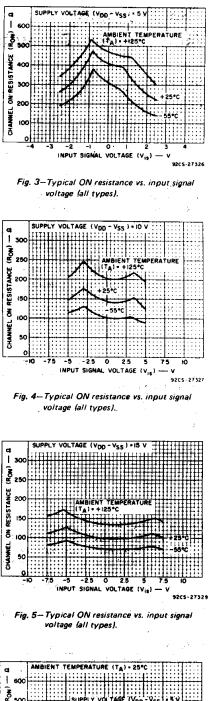
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 $^{st}$  Determined by minimum feasible leakage measurement for automatic testing.

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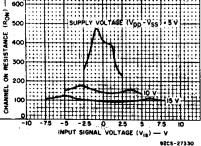


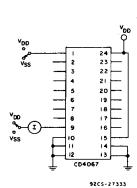
Fig. 6-Typical ON resistance vs. input signal voltage (all types).

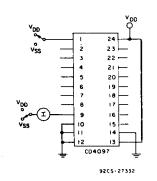
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#### ELECTRICAL CHARACTERISTICS (Cont'd)

CHARAC- TERISTIC			IS	LIMITS AT INDICATED TEMPERATURES							Units
	V <sub>is</sub>	v <sub>ss</sub>	VDD	-55	-40	+85	+125		+25		
	(V)	(V)	(V)					Min.	Тур.	Max.	
Input Current, I <sub>IN</sub> Max.	V <sub>IN</sub> = 0, 18 V 18			±0.1	±0.1	±1	±1		±10-5	±0.1	μΑ
Propagation Delay Time: Address or	R <sub>L</sub> -10 50 pF, t	KΩ,C <sub>L</sub> − t <sub>r</sub> ,t <sub>f</sub> =20 ns									
Inhibit-to-		0	5	-			-	-	325	650	
Signal OUT (Channel		0	10		ł	_	_	_	135	270	ns
turning ON)		0	15	-	_				95	190	1
Address or Inhibit-to-		0 Ω,C <sub>L</sub> = t <sub>r</sub> ,t <sub>f</sub> =20 ns									
Signal OUT		0	5	1 -	_	→ <sup>`</sup>	-		220	440	
(Channel		0	10	-	_		-	—	90	180	ns
turning OFF)		0	15	-		-	_		65	130	
Input Capaci- tance, C <sub>IN</sub>	Any A Inhibit		-		_		5	7.5	pF		

#### TEST CIRCUITS



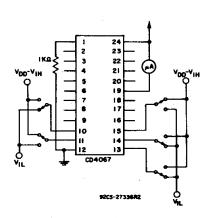


COMMERCIAL CMOS HIGH VOLTAGE ICS

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#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V <sub>DD</sub> )
Voltages referenced to V <sub>SS</sub> Terminal)0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS
DC INPUT CURRENT, ANY ONE INPUT
POWER DISSIPATION PER PACKAGE (PD):
For $T_A = -55^{\circ}C$ to $+100^{\circ}C$
For T <sub>A</sub> = +100 <sup>o</sup> C to +125 <sup>o</sup> CDerate Linearity at 12mW/ <sup>o</sup> C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T <sub>A</sub> = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (T <sub>A</sub> )
STORAGE TEMPERATURE RANGE (T <sub>stg</sub> )
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max



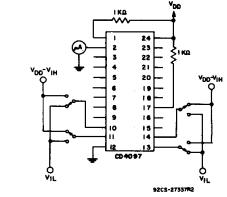
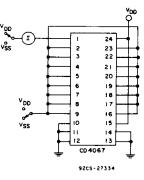


Fig. 8—Input voltage-measure <2 µA on all OFF channels (e.g., channel 12).

Fig. 7-OFF channel leakage current-any channel OFF.



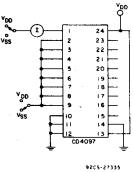


Fig. 9-OFF channel leakage current-all channels OFF.



#### ELECTRICAL CHARACTERISTICS (Cont'd)

			TE	ST COND	TIONS	-	1.1.	
CHARAC- TERISTIC	V <sub>is</sub> V <sub>DD</sub> R <sub>L</sub> (V) (V) (ΚΩ)				-	TYPICAL VALUES	UNITS	
Cutoff	5 <b>®</b>	10	1					
(3-dB) Frequency				V <sub>OS</sub> at Common OUT/IN CD4067 CD4097 V <sub>OS</sub> at Any Channel			14	
Channel ON	20 log	$\frac{V_{os}}{V_{is}} = -3$	3 dB				20	MHż
(Sine Wave Input)	20109	V <sub>is</sub>	5 0 0				60	141112
Total	2•	5				·	0.3	
Harmonic	3 <b>•</b>	10	10				0.2	
Distortion, THD	5 <sup>●</sup>	15					0.12	%
	f <sub>is</sub> = 1 k'Hz sine wave							
40-dB	5 <b>°</b>	10	1					
Feedthrough	$20 \log \frac{V_{os}}{V_{is}} = -40 \text{ dB}$			V at Co	mmon OUT/IN	20		
Frequency (All Channels						12	MHz	
OFF				V <sub>os</sub> at An	y Channel	8		
	5 <b>•</b>	10	1		•			
Signal Cross-	······			Between A	Any 2 Channels <sup>▲</sup>	1		
talk (Fre-	V <sub>os</sub> 40		<b>A</b> 10	Between	Measured on Common		10	
quency at —40 dB)	2010g	$\overline{v_{is}}^{=-2}$	+U 0 B	Sections CD4097 Only	Measured on A Channel	18	MHz	
	-	10	10*					
Address-or-	V <sub>SS</sub> =0, t <sub>r</sub> ,t <sub>f</sub> =20 ns, V <sub>C</sub> =V <sub>DD</sub> V <sub>SS</sub>							I
Inhibit-to-						75	mV	
Signal Crosstalk	(Squar	re Wave)						(Peak)
Crosstalk								

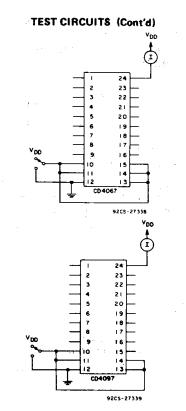


Fig. 10- Quiescent device current.

Peak-to-peak voltage symmetrical about

۸ Worst case.

Both ends of channel.

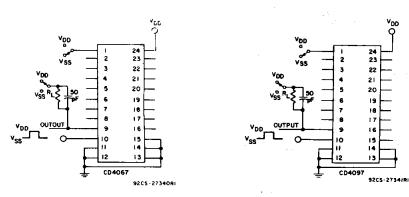


Fig. 11-Turn-on and turn-off propagation delay-address select input to signal output (e.g. measured on channel 0).

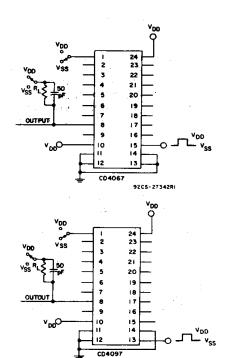
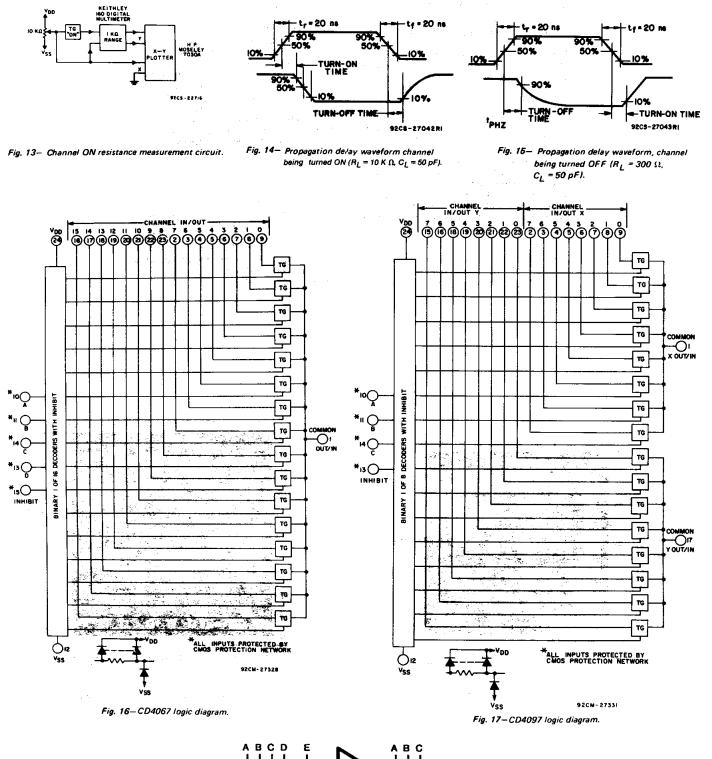


Fig. 12-Turn-on and turn-off propagation delayinhibit input to signal output (e.g. measured on channel 1).

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COMMERCIAL CMOS HIGH VOLTAGE ICS

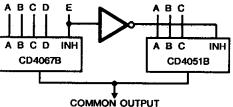


Fig. 18-24-to-1 MUX Addressing

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#### SPECIAL CONSIDERATIONS

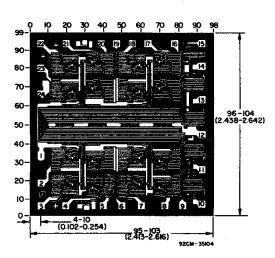
In applications where separate power sources are used to drive VDD and the signal inputs, the VDD current capability should exceed VDD/RL (RL=effective external load). This provision avoids permanent current flow or clamp action on the VDD supply when power is applied or removed from the CD4067B or CD4097B.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned on or off by an address input, there is a momentary conductive path from the channel to VSS, which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to VSS.

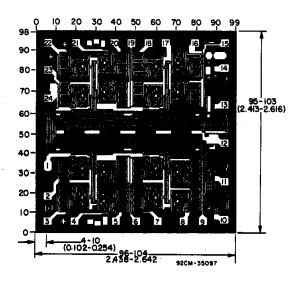
The amount of charge dumped is mostly a function of the signal level above VSS. Typically, at  $V_{DD}-V_{SS}$ =10 V, a 100-pF

capacitor connected to the input or output of the channel will lose 3-4% of its voltage at the moment the channel turns on or off. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1-2  $\mu$ s. When the inhibit signal turns a channel off, there is no charge dumping to VSS. Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

In certain applications, the external load-resistor current may include both  $V_{DD}$  and signal-line components. To avoid drawing  $V_{DD}$  current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from RON values shown in ELECTRICAL CHARACTERISTICS CHART). No  $V_{DD}$  current will flow through RL if the switch current flows into terminal 1 on the CD4067B, terminals 1 and 17 on the CD4097B.



Dimensions and pad layout for CD4067BH.



Dimensions and pad layout for CD4097BH,

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils  $(10^{-3} \text{ inch})$ .

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